

L Number	Hits	Search Text	DB	Time stamp
1	0	(etch adj stop) and (etching adj finfet adj gate)	USPAT	2004/06/20 11:24
2	0	(etch adj st p) and (etching adj finfet)	USPAT	2004/06/20 11:25
3	0	(etch adj st p) and finfet and gate and anti-reflective and c ating and ARC	USPAT	2004/06/20 11:26
4	0	(etch adj stop) and (fin adj field adj effect adj transistor) and gate and anti-reflective and c ating and ARC	USPAT	2004/06/20 11:27
5	0	(fin adj field adj effect adj transistor) and gate and anti-reflective and coating and ARC and etch	USPAT	2004/06/20 11:27
6	6	(fin adj field adj effect adj transistor)	USPAT	2004/06/20 12:05
7	6	((fin adj field adj effect adj transistor)) and (ARC or anti or reflective or coating or gate or electrode or etch or etching or stop or stopper or shape or photo or resist or polysilicon or Ti or TiN or SiN or CF or HBr or FinFET)	USPAT	2004/06/20 12:31
8	4	(fin adj field adj effect adj transistor) and (etch adj stop)	USPAT	2004/06/20 12:05
9	1	("6657252").PN.	USPAT	2004/06/20 12:31
10	1316	438/197	USPAT	2004/06/20 12:31
11	1203	438/199	USPAT	2004/06/20 12:31
12	165	438/206	USPAT	2004/06/20 12:32
13	563	438/584	USPAT	2004/06/20 12:32
14	1184	438/595	USPAT	2004/06/20 12:32
15	870	438/689	USPAT	2004/06/20 12:32
16	505	438/740	USPAT	2004/06/20 12:32

6/20/04